

APPARATUS AND METHOD FOR IN-SITU ENDPOINT DETECTION FOR CHEMICAL MECHANICAL POLISHING OPERATIONS

ABSTRACT OF THE DISCLOSURE

5 An apparatus and method of chemical mechanical polishing (CMP) of a wafer
employing a device for determining, in-situ, during the CMP process, an endpoint where the
process is to be terminated. This device includes a laser interferometer capable of generating
a laser beam directed towards the wafer and detecting light reflected from the wafer, and a
window disposed adjacent to a hole formed through a platen. The window provides a
10 pathway for the laser beam during at least part of the time the wafer overlies the window.

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